

# MC14012B

## Dual 4-Input NAND Gates

The MC14012B dual 4-input NAND gates are constructed with P-Channel and N-Channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

### Features

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low-Power TTL Loads or One Low-Power Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices
- Pb-Free Packages are Available

### MAXIMUM RATINGS (Voltages Referenced to $V_{SS}$ )

Symbol	Parameter	Value	Unit
$V_{DD}$	DC Supply Voltage Range	-0.5 to +18.0	V
$V_{in}, V_{out}$	Input or Output Voltage Range (DC or Transient)	-0.5 to $V_{DD} + 0.5$	V
$I_{in}, I_{out}$	Input or Output Current (DC or Transient) per Pin	$\pm 10$	mA
$P_D$	Power Dissipation, per Package (Note 1)	500	mW
$T_A$	Ambient Temperature Range	-55 to +125	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65 to +150	$^{\circ}C$
$T_L$	Lead Temperature (8-Second Soldering)	260	$^{\circ}C$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### 1. Temperature Derating:

Plastic "P and D/DW" Packages: - 7.0 mW/ $^{\circ}C$  From 65 $^{\circ}C$  To 125 $^{\circ}C$

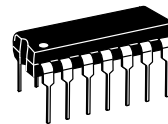
This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either  $V_{SS}$  or  $V_{DD}$ ). Unused outputs must be left open.

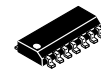
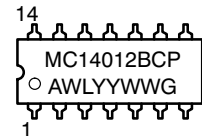


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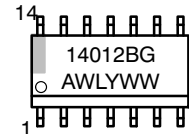
### MARKING DIAGRAMS



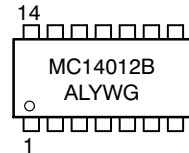
PDIP-14  
P SUFFIX  
CASE 646



SOIC-14  
D SUFFIX  
CASE 751A



SOEIAJ-14  
F SUFFIX  
CASE 965



A = Assembly Location  
WL, L = Wafer Lot  
YY, Y = Year  
WW, W = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

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## MC14012B Dual 4-Input NAND Gate

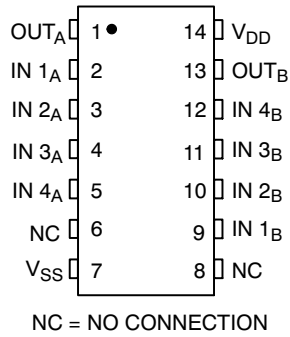


Figure 1. Pin Assignment

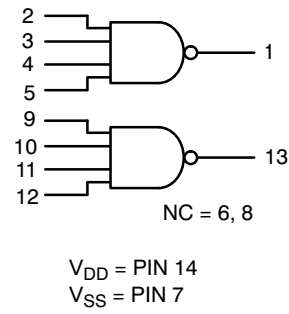


Figure 2. Logic Diagram

### ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC14012BCP	PDIP-14	25 Units / Rail
MC14012BCPG	PDIP-14 (Pb-Free)	
MC14012BD	SOIC-14	55 Units / Rail
MC14012BDG	SOIC-14 (Pb-Free)	
MC14012BDR2	SOIC-14	2500 Units / Tape & Reel
MC14012BDR2G	SOIC-14 (Pb-Free)	
MC14012BFEL	SOEIAJ-14	2000 Units / Tape & Reel
MC14012BFELG	SOEIAJ-14 (Pb-Free)	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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## ELECTRICAL CHARACTERISTICS (Voltages Referenced to V<sub>SS</sub>)

Characteristic	Symbol	V <sub>DD</sub> Vdc	- 55°C		25°C			125°C		Unit	
			Min	Max	Min	Typ (Note 2)	Max	Min	Max		
Output Voltage V <sub>in</sub> = V <sub>DD</sub> or 0	"0" Level	V <sub>OL</sub>	5.0	-	0.05	-	0	0.05	-	0.05	Vdc
			10	-	0.05	-	0	0.05	-	0.05	
15			-	0.05	-	0	0.05	-	0.05		
V <sub>in</sub> = 0 or V <sub>DD</sub>	"1" Level	V <sub>OH</sub>	5.0	4.95	-	4.95	5.0	-	4.95	-	Vdc
			10	9.95	-	9.95	10	-	9.95	-	
			15	14.95	-	14.95	15	-	14.95	-	
Input Voltage (V <sub>O</sub> = 4.5 or 0.5 Vdc) (V <sub>O</sub> = 9.0 or 1.0 Vdc) (V <sub>O</sub> = 13.5 or 1.5 Vdc)	"0" Level	V <sub>IL</sub>	5.0	-	1.5	-	2.25	1.5	-	1.5	Vdc
			10	-	3.0	-	4.50	3.0	-	3.0	
15			-	4.0	-	6.75	4.0	-	4.0		
(V <sub>O</sub> = 0.5 or 4.5 Vdc) (V <sub>O</sub> = 1.0 or 9.0 Vdc) (V <sub>O</sub> = 1.5 or 13.5 Vdc)	"1" Level	V <sub>IH</sub>	5.0	3.5	-	3.5	2.75	-	3.5	-	Vdc
			10	7.0	-	7.0	5.50	-	7.0	-	
			15	11	-	11	8.25	-	11	-	
Output Drive Current (V <sub>OH</sub> = 2.5 Vdc) (V <sub>OH</sub> = 4.6 Vdc) (V <sub>OH</sub> = 9.5 Vdc) (V <sub>OH</sub> = 13.5 Vdc)	Source	I <sub>OH</sub>	5.0	-3.0	-	-2.4	-4.2	-	-1.7	-	mAdc
			5.0	-0.64	-	-0.51	-0.88	-	-0.36	-	
10			-1.6	-	-1.3	-2.25	-	-0.9	-		
15			-4.2	-	-3.4	-8.8	-	-2.4	-		
(V <sub>OL</sub> = 0.4 Vdc) (V <sub>OL</sub> = 0.5 Vdc) (V <sub>OL</sub> = 1.5 Vdc)	Sink	I <sub>OL</sub>	5.0	0.64	-	0.51	0.88	-	0.36	-	mAdc
			10	1.6	-	1.3	2.25	-	0.9	-	
			15	4.2	-	3.4	8.8	-	2.4	-	
Input Current	I <sub>in</sub>	15	-	±0.1	-	±0.00001	±0.1	-	±1.0	μAdc	
Input Capacitance (V <sub>in</sub> = 0)	C <sub>in</sub>	-	-	-	-	5.0	7.5	-	-	pF	
Quiescent Current (Per Package)	I <sub>DD</sub>	5.0	-	0.25	-	0.0005	0.25	-	7.5	μAdc	
		10	-	0.5	-	0.0010	0.5	-	15		
		15	-	1.0	-	0.0015	1.0	-	30		
Total Supply Current (Notes 3, 4) (Dynamic plus Quiescent, Per Gate, C <sub>L</sub> = 50 pF)	I <sub>T</sub>	5.0	I <sub>T</sub> = (0.3 μA/kHz) f + I <sub>DD</sub> /N							μAdc	
10	I <sub>T</sub> = (0.6 μA/kHz) f + I <sub>DD</sub> /N										
15	I <sub>T</sub> = (0.9 μA/kHz) f + I <sub>DD</sub> /N										

2. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.
3. The formulas given are for the typical characteristics only at 25°C.
4. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I<sub>T</sub> is in μA (per package), C<sub>L</sub> in pF, V = (V<sub>DD</sub> - V<sub>SS</sub>) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

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## SWITCHING CHARACTERISTICS (Note 5) ( $C_L = 50 \text{ pF}$ , $T_A = 25^\circ\text{C}$ )

Characteristic	Symbol	$V_{DD}$ Vdc	Min	Typ (Note 6)	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	$t_{TLH}$	5.0 10 15	- - -	100 50 40	200 100 80	ns
Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	$t_{THL}$	5.0 10 15	- - -	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH}, t_{PHL} = (0.90 \text{ ns/pF}) C_L + 115 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.36 \text{ ns/pF}) C_L + 47 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.26 \text{ ns/pF}) C_L + 37 \text{ ns}$	$t_{PLH}, t_{PHL}$	5.0 10 15	- - -	160 65 50	300 130 100	ns

5. The formulas given are for the typical characteristics only at  $25^\circ\text{C}$ .

6. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

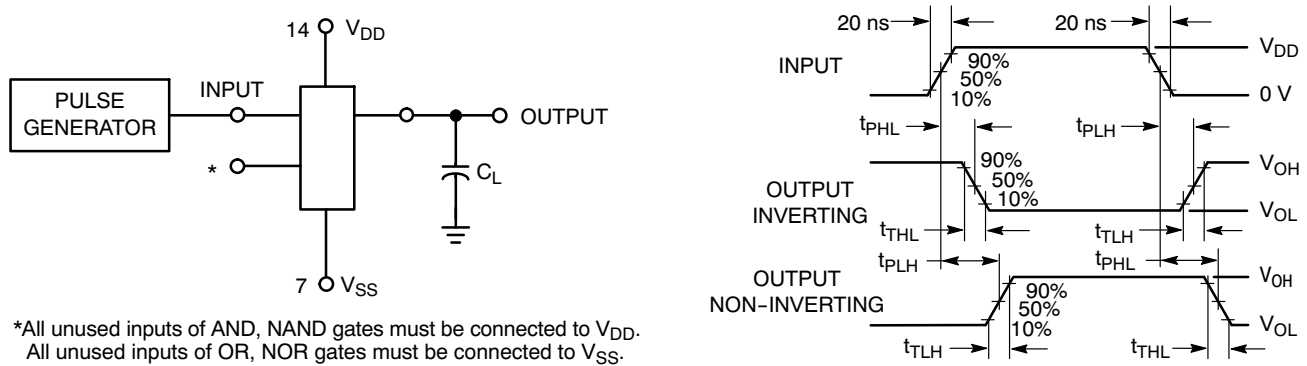


Figure 3. Switching Time Test Circuit and Waveforms

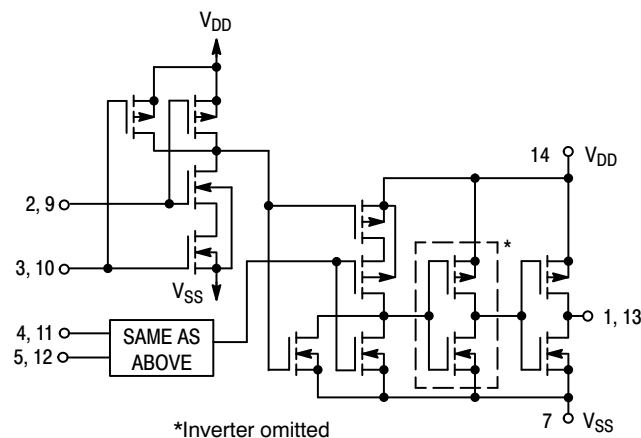
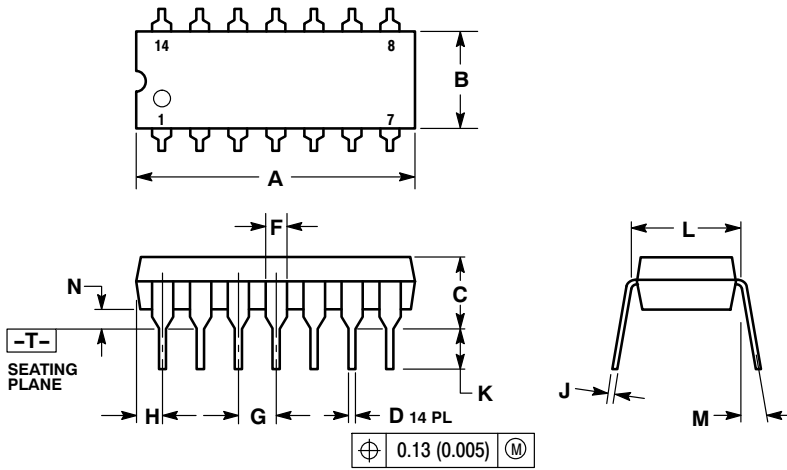


Figure 4. Circuit Schematic - One of Two Gates Shown

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## PACKAGE DIMENSIONS

**PDIP-14**  
CASE 646-06  
ISSUE P



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	---		10°	
N	0.015	0.039	0.38	1.01